

AMENDMENTS TO THE CLAIMS

Claims 1-14. (Canceled).

15. (Currently Amended) The method of Claim 19 [[14]] further comprising:

forming an orifice layer over said thin film layers, said orifice layer defining a plurality of ink ejection chambers, wherein an ink jet ejection element is included within each chamber ~~having within it an ink ejection element~~, said orifice layer further defining a nozzle for each ink ejection chamber.

16. (Currently Amended) The method of Claim 19 [[14]] wherein said ink ejection elements reside on a silicon bridge between two portions of thicker silicon.

17. (Currently Amended) The method of Claim 19 [[14]] wherein said forming at least one opening comprises etching a trench in said SOI ~~silieon~~ substrate.

18. (Original) The method of Claim 17 wherein said trench extends at least a length of a row of said ink ejection elements.

19. (Currently Amended) ~~The method of Claim 14 wherein said printhead substrate is a silicon-on-insulator (SOI) substrate~~ A method of forming a printhead comprising:

providing a silicon-on-insulator (SOI) substrate comprising a first silicon layer, a thinner second silicon layer, and an oxide layer between said first silicon layer and said second silicon layer; ~~and said step of forming at least one opening in said substrate comprises:~~

- forming a plurality of thin film layers on a first surface of said substrate, at least one of said layers forming a plurality of ink ejection elements;

forming ink feed holes through said thin film layers; and
forming at least one opening in said substrate by (a) etching said first silicon layer of said SOI substrate using a wet etch to etch a trench in said first silicon layer extending to said oxide layer; (b) etching at least one opening in said oxide layer; and (c) etching at least one opening in said second silicon layer to form an ink path between a backside of said SOI substrate and a topside of said SOI substrate to provide an ink path from a second surface of said substrate, through said substrate, and to said ink feed holes formed in said thin film layers, wherein said plurality of ink ejection elements reside over a silicon layer.

20. (Original) The method of Claim 19 wherein said etching step (c) is performing using a wet etch.

21. (Original) The method of Claim 19 wherein said etching step (c) is performing using a dry etch.

Claims 22-26. (Canceled).